

ABSTRACT

A GaN-FET (10) having a small resistance at the time of conduction is disposed in the path of a main current that flows between an input terminal (11) and an output terminal 5 (12). Moreover, there are provided a Zener diode (ZD) and a resistor (R) for setting an output voltage (Vout). As a result, reduction of size and weight is realized, and design including radiation design can be conducted flexibly. Time and labor required for design are remarkably reduced.

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